

Silicon PNP Power Transistors

2SA1360

DESCRIPTION

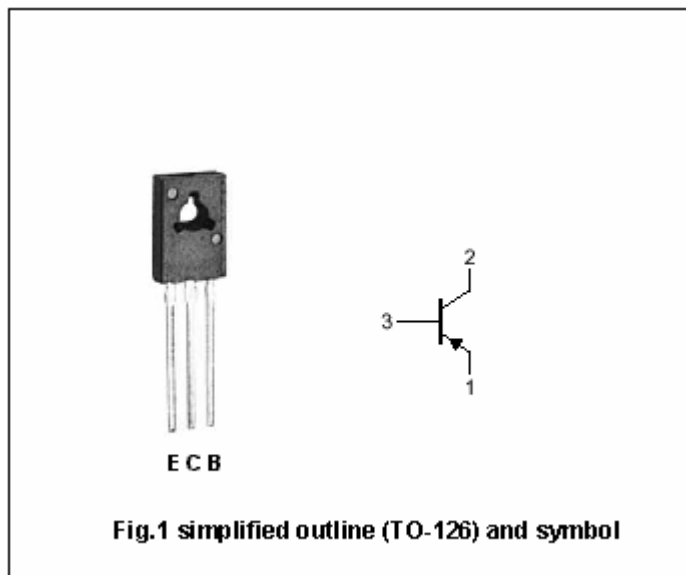
- With TO-126 package
- Complement to type 2SC3423
- High transition frequency

APPLICATIONS

- Audio frequency amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-50	mA
I_B	Base current		-5	mA
P_D	Total power dissipation	$T_a=25^\circ\text{C}$	1.2	W
		$T_C=25^\circ\text{C}$	5	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		$-55^\circ\text{C}+150^\circ\text{C}$	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA ; I _B =0	-150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-10mA; I _B =-1mA			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-10mA ; V _{CE} =-5V			-0.8	V
I _{CBO}	Collector cut-off current	V _{CB} =-150V; I _E =0			-0.1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.1	μA
h _{FE}	DC current gain	I _C =-10mA ; V _{CE} =-5V	80		240	
C _{ob}	Output capacitance	I _E =0 ; V _{CB} =-10V f=1MHz		2.5		pF
f _T	Transition frequency	I _C =-10mA ; V _{CE} =-10V		200		MHz

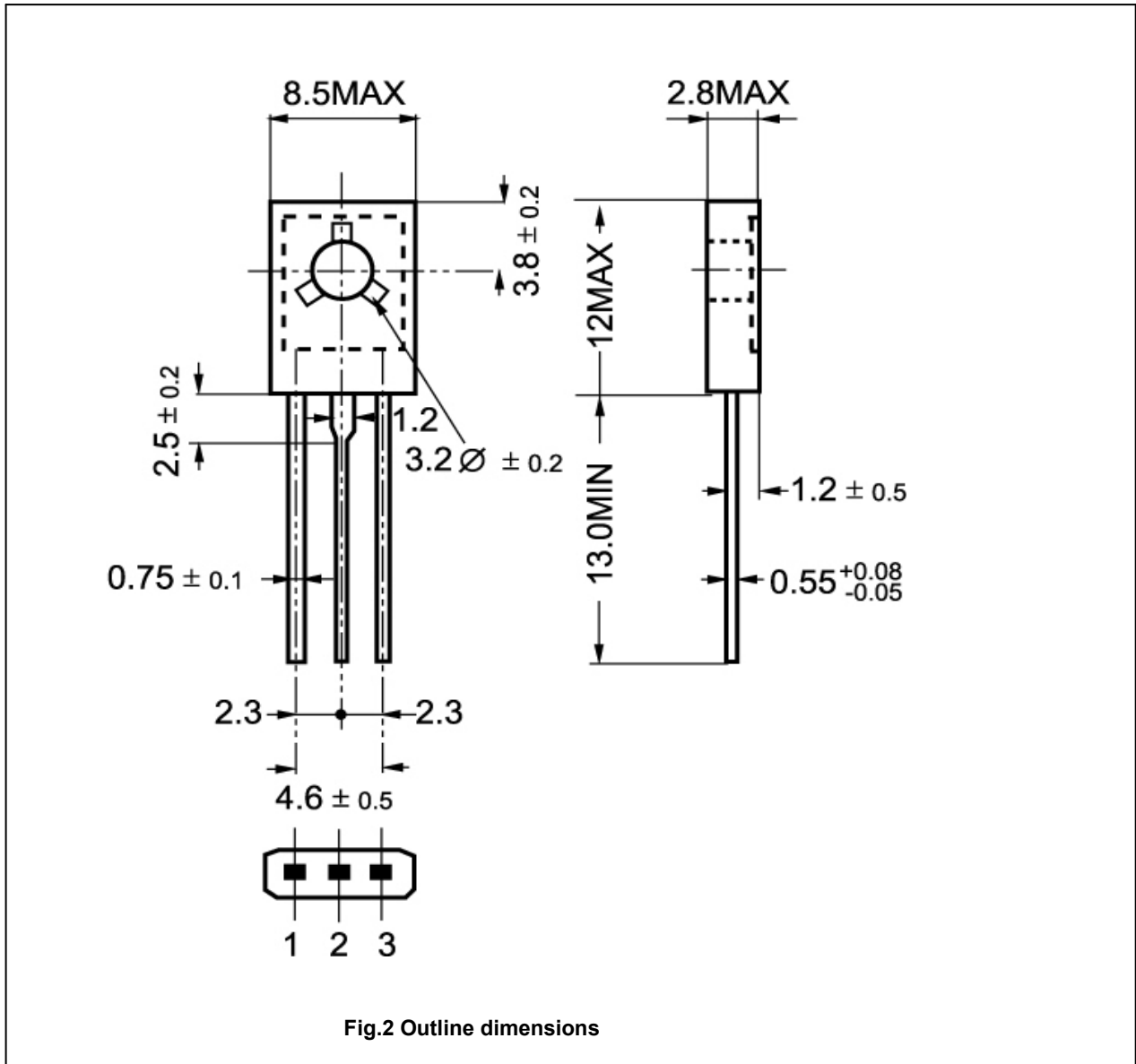
◆ h_{FE} Classifications

O	Y
80-160	120-240

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PACKAGE OUTLINE



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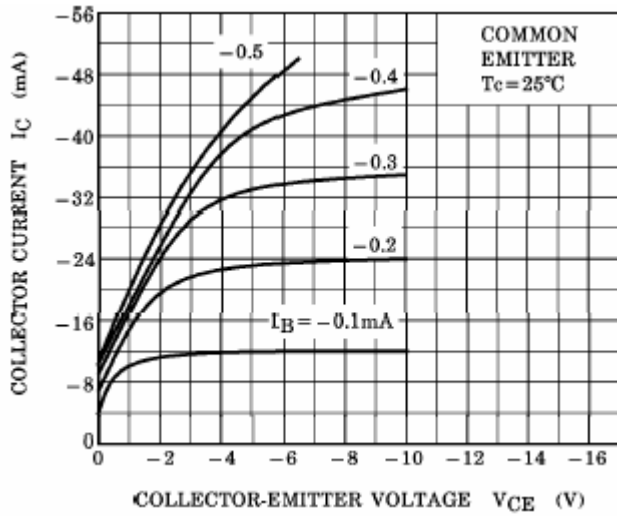


Fig.3 Static Characteristic

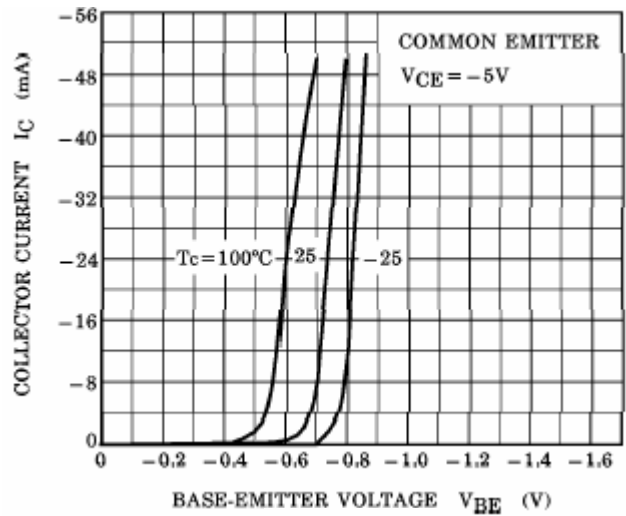


Fig.4 I_C - V_{BE}

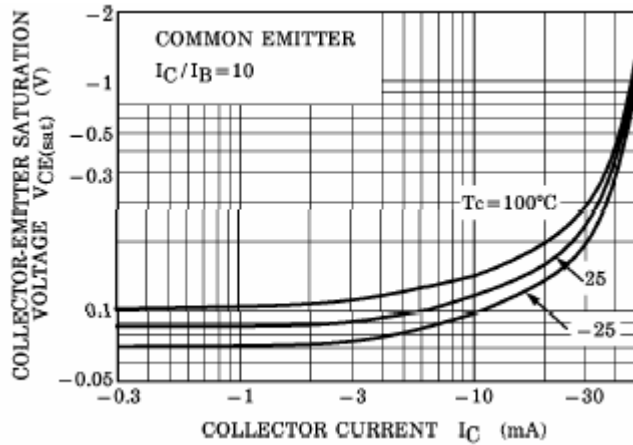


Fig.5 Collector-Emitter Saturation Voltage

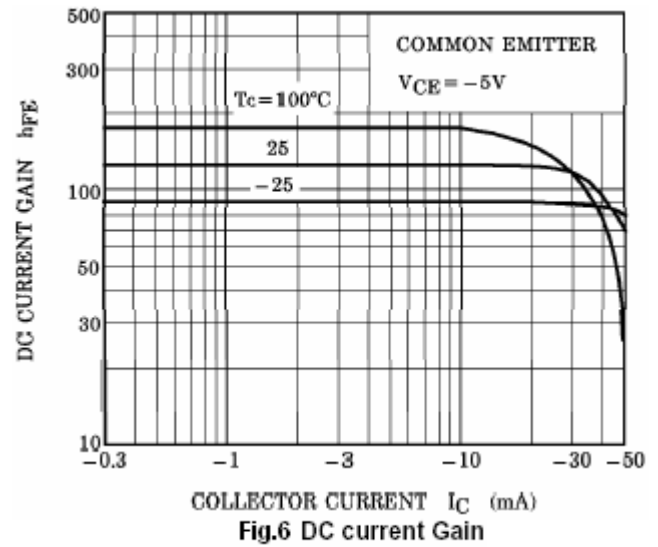


Fig.6 DC current Gain

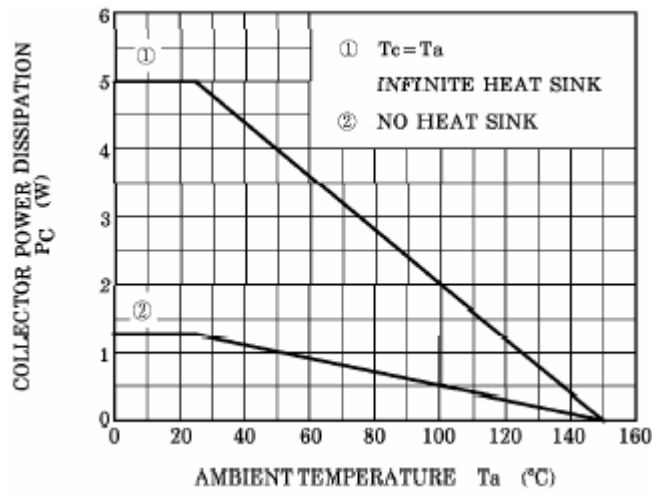


Fig.7 Power Derating